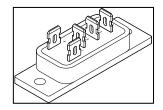
TECHNICAL DATA DATA SHEET 4253, REV -

THREE PHASE FULL WAVE BRIDGE RECTIFIER ASSEMBLY



DESCRIPTION: A 50 VOLT, 5000 NANOSECOND THREE PHASE BRIDGE RECTIFIER ASSEMBLY.

MAXIMUM RATINGS

All ratings are at $T_A = 25^{\circ}$ C unless otherwise specified.

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RATING	CONDITIONS	MIN	TYP	MAX	UNIT
Peak Inverse Voltage (PIV)	-	-	1	50	Vdc
Average DC Output Current (T_C = Case Temp) (I_o)	$T_{C} = 55$ °C $T_{C} = 100$ °C $T_{C} = 125$ °C	-	ı	18.5 12.5 9.0	Amps
Average DC Output Current Ambient Temp. (no heat sink) (I _o)	$T_A = 25 ^{\circ}\text{C}$ $T_A = 55 ^{\circ}\text{c}$ $T_A = 100 ^{\circ}\text{c}$	-	1	6.0 5.0 3.0	Amps
Peak Single Cycle Surge Current (I _{FSM})	t _p = 8.3 ms Single Half Cycle Sine Wave, Superimposed On Rated Load	-	-	150	Amps(pk)
Thermal Resistance (θ _{JL})	-	-	-	2.5	°C/W
Operating and Storage Temp. (T _{op} & T _{stg})	-	-55	-	+150	°C

ELECTRICAL CHARACTERISTICS

CHARACTERISTICS	CONDITIONS	MIN	TYP	MAX	UNIT
Maximum Forward Voltage (V _f)	I _f = 3A (300 μsec pulse, duty cycle < 2%)	-	-	1.0	Volts
Maximum Instantaneous Reverse Current At Rated (PIV)	T _A = 25° C	-	-	3.0	μAmps
	T _A = 100° C			60	
Reverse Recovery Time (t _{rr})	I _f = 0.5A, I _r = 1.0A, I _{rr} = 0.25A	-	-	2000	nsec

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MECHANICAL DIMENSIONS: In Inches / mm

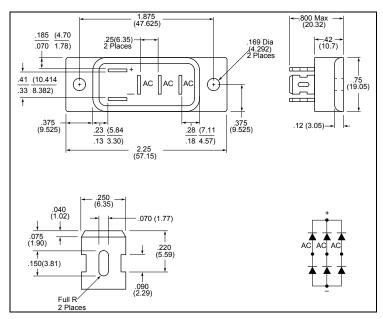


FIG. 404

Note: Case finish - Black Anodized

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